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The invention refers to the semiconductor production technology, in particular to the processes for semiconductor nanostructures obtaining.

Summary of the invention consists in that the process for obtaining semiconductor nanostructures includes the deposition of a mask onto one of the surfaces of the semiconductor plate, the ion implantation, the electrochemical treatment and removal of the mask. The ion implantation is carried out at the ion energy of at least 30 keV with a dose of up to 10^{11} cm⁻², and the electrochemical treatment is carried out at the current passage with a density of at least 100 mA/cm².

Claims: 1

Fig.: 1